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RP			Kameyama, S. et al.: "Base Link-Up Process Technology for Self-Aligned Double Diffusion Bipolar Transistors", IEEE, 1987, pp. 27-30;					
RI	Ø		Nakamae, M.: "Recent Progress and Future Prospect for VLSI Si Biopolar Transistors", IEEE, 1987, pp. 5-6;					
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RP	c <sup>f</sup>	Yamaguchi, T. et al.: "Process and Device Performance of a High-Speed Double Poly-Si Bipolar Technology Using Borosenic-Poly Process with Coupling-Base Implant", IEEE, Vol. 35, No. 8, August 1988, pp. 1247-1256;							
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RP	5	Van der Velden, J. et al.: "Basic: An Advanced High-Peformance Bipolar Process", IEEE, 1989, pp. 9.4.1-9.4.4;						
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with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								
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RP	Shiba, T. et al.: "Base Peripheral Effects on High Performance Self-Aligned Bipolar Devices (SICOS)", Scripta Technica, Inc., 1990, pp. 100-105;							
RP	IJ	Hayden, J. D. et al.: "A New Technique for Forming a Shallow Link Base in a Double Polysilicon Bipolar Transistor", IEEE, 1994, pp. 63-68;						
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RP	./	Park, J. et al.: "Ultrashallow p <sup>†</sup> /n Junction Formation by 0.5-1 keV lon Implantation", Japanese Journal of Applied Physics, Vol. 37, No. 11B, 1998,						
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